

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (previously presented) An array of MRAM-cells provided with a security device for destroying data stored in the MRAM-cells when the array is subject to tampering, wherein the security device is a magnetic device.
2. (previously presented) An array of MRAM-cells according to claim 1, wherein the security device comprises a magnetic field source in combination with a first soft-magnetic flux-closing layer.
3. (previously presented) An array of MRAM-cells according to claim 2, wherein the magnetic field source is a permanent magnet.
4. (previously presented) An array 3 of MRAM-cells according to claim 2, wherein the magnetic field source is an electromagnet.
5. (currently amended) An array of MRAM-cells according to ~~any of the previous claims~~claim 1, wherein the security device ~~4 is built near~~ is coupled with the array of MRAM-cells.
6. (previously presented) An array of MRAM-cells according to claim 1, the array being built on a substrate, wherein the security device is built at the same side of the substrate as the MRAM-cells.
7. (previously presented) An array of MRAM-cells according to claim 1, the array being built on a substrate, wherein the security device is built at the opposite side of the

substrate as the MRAM-cells.

8. (currently amended) An array of MRAM-cells according to claim 2, wherein the first soft-magnetic flux-closing layer ~~(18)~~ is so as to separate from the magnetic field source when the array of MRAM-cells is tampered with.

9. (currently amended) An array of MRAM-cells, according to claim 1, wherein the security device ~~(14)~~ furthermore comprises a magnetic field shaping device.

10. (previously presented) An array of MRAM-cells according to claim 9, wherein the magnetic field shaping device is a second soft-magnetic layer, the magnetic field source and first soft-magnetic layer being located adjacent the array of MRAM-cells at one side, and the second soft-magnetic layer being located adjacent the array of MRAM-cells at the opposite side thereof.

11. (previously presented) An array of MRAM-cells, according to claim 2, wherein the first soft-magnetic layer and/or the second soft-magnetic layer are part of a shielding layer of the MRAM-array.

12. (previously presented) A method for protecting from unauthorised read-out an array of MRAM-cells having a data content, the method comprising automatically destroying the data content of at least some of the MRAM-cells by a magnetic field when the array is tampered with.

13. (previously presented) A method according to claim 12, wherein the magnetic field is generated at the MRAM-cells by separating a soft-magnetic flux-closing layer from a magnetic field source.

14. (previously presented) A method according to claim 12 wherein the magnetic field at the MRAM-cells is enhanced by a magnetic field shaping device located adjacent the array of MRAM-cells.

15. (new) A tamper-resistant memory device comprising:
a plurality of MRAM-cells; and
at least one security device coupled with said MRAM-cells, said security device including a magnetic source and a shielding layer;
wherein the shielding layer deviates magnetic field lines of the magnet, such that the plurality of MRAM-cells are unaffected by said magnetic field lines; and
further wherein at least partial removal of said shielding layer causes said magnetic field lines to affect at least some of the plurality of MRAM-cells, when said memory device is subject to tampering.
16. (new) The tamper-resistant memory device of claim 15, wherein the magnetic source is a permanent magnet.
17. (new) The tamper-resistant memory device of claim 15, wherein the shielding layer is a first soft-magnetic flux-closing layer.
18. (new) The tamper-resistant memory device of claim 15, wherein said memory device is configured to cause said shielding layer to separate from said magnetic source when the memory device is subject to tampering.
19. (new) The tamper-resistant memory device of claim 15 further comprising a magnetic field shaping device.
20. (new) The tamper-resistant memory device of claim 18, wherein the magnetic field shaping device is a second soft-magnetic layer, the magnetic field source and first soft-magnetic layer being located adjacent the array of MRAM-cells at one side, and the second soft-magnetic layer being located adjacent the array of MRAM-cells at the opposite side thereof.